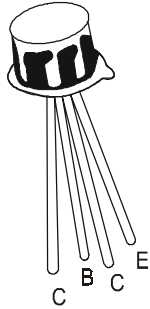


## NPN SILICON PLANAR RF TRANSISTOR

**BF115**



**TO-72  
Metal Can Package**

### ABSOLUTE MAXIMUM RATINGS (Ta=25°C unless specified otherwise)

DESCRIPTION	SYMBOL	VALUE	UNIT
Collector Base Voltage	$V_{CBO}$	50	V
Collector Emitter Voltage	$V_{CEO}$	30	V
Emitter Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	30	mA
Base Current Continuous	$I_B$	1	mA
Total Power Dissipation @ Ta=45°C	$P_D$	145	mW
Operating & Storage Junction Temperature Range	$T_j, T_{stg}$	-55 to +175	°C

### THERMAL RESISTANCE

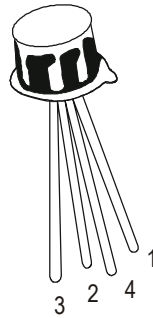
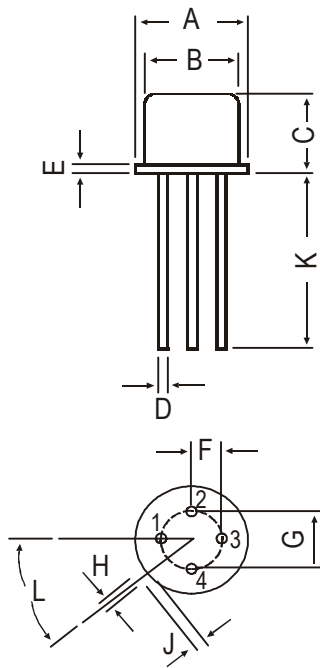
Junction to Ambient	$R_{th(j-a)}$	900	°C/W
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### ELECTRICAL CHARACTERISTICS (Ta=25° C unless specified otherwise )

DESCRIPTION	SYMBOL	TEST CONDITION	VALUE			UNIT
			MIN	TYP	MAX	
Collector Emitter Breakdown Voltage	BV <sub>CEO</sub> *	I <sub>C</sub> =2mA, I <sub>B</sub> =0	30			V
Collector Base Breakdown Voltage	BV <sub>CBO</sub>	I <sub>C</sub> =10μA, I <sub>E</sub> =0	50			V
Emitter Base Breakdown Voltage	BV <sub>EBO</sub>	I <sub>E</sub> =10μA, I <sub>C</sub> =0	5			V
Collector Cut off Current	I <sub>CBO</sub>	V <sub>CB</sub> =20V, I <sub>E</sub> =0, Ta=175°C		0.5		μA
DC Current Gain	h <sub>FE</sub>	I <sub>C</sub> =1mA, V <sub>CE</sub> =10V	48		167	
		I <sub>C</sub> =20mA*, V <sub>CE</sub> = 2V	40			
Base Emitter On Voltage	V <sub>BE(on)</sub>	I <sub>C</sub> =1mA, V <sub>CE</sub> =10V	600	700	740	mV
		I <sub>C</sub> =20mA, V <sub>CE</sub> = 2V*			1000	mV
<b><u>DYNAMIC CHARACTERISTICS</u></b>						
Transition Frequency	f <sub>T</sub>	I <sub>C</sub> =1.0mA, V <sub>CE</sub> =10V, f=100MHz		230		MHz
Feedback Capacitance	C <sub>re</sub>	V <sub>CB</sub> =10V, I <sub>C</sub> =1mA, f=0.45MHz		0.65	0.8	pF
Noise Figure	NF	V <sub>CE</sub> =10V, I <sub>C</sub> =1mA, Rg=300KΩ, f=200KHz		1.5		dB
		f=1MHz		1.2		dB

**Pulse Test: pulse Width  $\leq 300\mu S$ , Duty Cycle  $\leq 2\%$**

## TO-72 Metal Can Package



## PIN CONFIGURATION

1. EMITTER
2. BASE
3. COLLECTOR
4. CASE

All dimensions in mm.

DIM	MIN.	MAX.
A	5.24	5.84
B	4.52	4.95
C	4.31	5.33
D	0.40	0.53
E	—	0.76
F	1.14	1.39
G	2.28	2.97
H	0.91	1.17
J	0.71	1.22
K	12.70	—
L	12 DEG	48 DEG

## Packing Detail

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
TO-72	1 K/Polybag	325 gm/1K pcs	3" x 7.5" x 7.5"	5K	17" x 15" x 13.5"	80K	32 kgs

### **Disclaimer**

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